

Effects of short-range attachment barriers on submonolayer growth

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Abstract:

A variety of effects can lead to short-range attachment barriers in thin-film growth. While it has been predicted that the exponent which describes the dependence of the island density on deposition rate in the submonolayer regime (where $n < n_c$) crosses over from the diffusion-limited value (where n_c is the critical island size) in the absence of an attachment barrier to the attachment-limited value for a strong attachment barrier, this prediction has not been confirmed. Furthermore, the dependence of the effective value of n on the barrier strength and ratio (where ν is the [monomer](#) hopping rate) has not been studied. Here we consider the effects of attachment barriers in irreversible growth ($\nu = 0$) for both the case of a barrier to island nucleation and attachment as well as that of an island attachment barrier but no nucleation barrier. Our results indicate that in both cases the effective value of n increases with increasing R to a maximum value which depends on barrier strength before decreasing very slowly toward the diffusion-limited value. In addition, both n and ν increase as the barrier strength increases. The results of self-consistent rate-equation calculations are also presented and good agreement is found with our simulations. We also present a scaling analysis for the dependence of n on the barrier strength for arbitrary critical island-size and good agreement is found with our simulation results for the case in which there is both a nucleation barrier and a barrier to island attachment.